

# A 10kfps 32x32 Integrated Test Platform for Electrical Characterization of Imagers

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- 1** Introduction
- 2** ITP Architecture
- 3** ITP Pixel Cell
- 4** Low-Cost CMOS Integration
- 5** Experimental Results
- 6** Conclusions

## Introduction

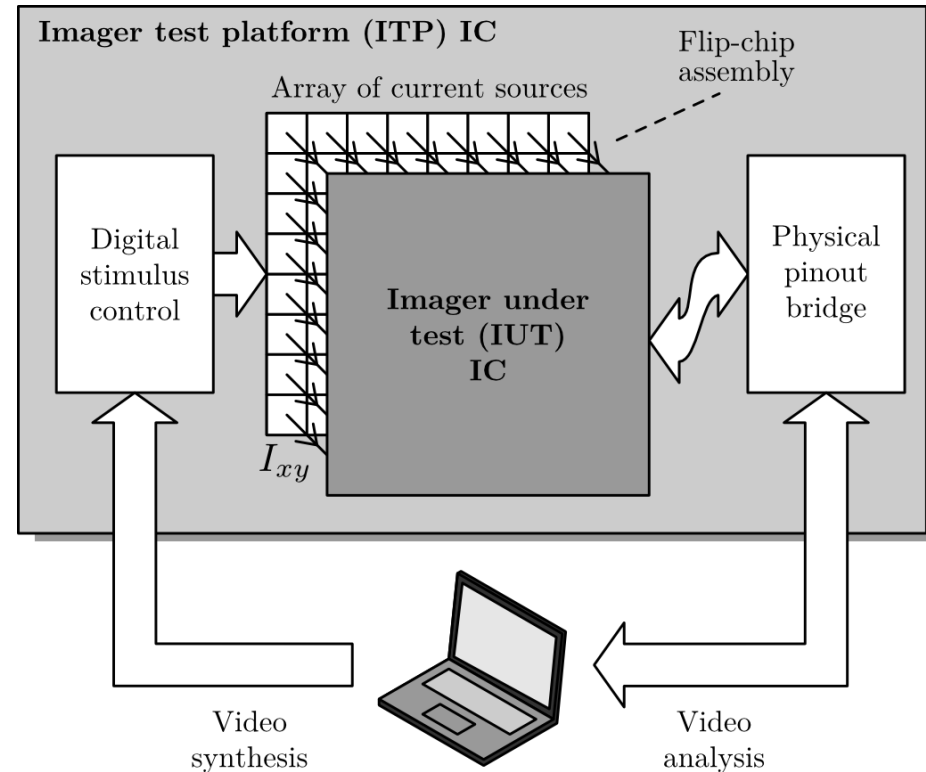
- ▶ How to **characterize** imager response to **image patterns** and **motion sequences**?

### 1. Standard approach: Optical stimulation (LED arrays, TFT displays, mechanical choppers...)

- ▼ **Bulky** + optical chain **uncertainty**
- ▼ Requires detector: **Not** suitable for **electrical direct tests**

### 2. Our proposal: Electrical Imager test platform (ITP) custom IC + Imager under test (IUT) attached pixel-by-pixel to ITP by flip-chip packaging

- ▲ **Compact** setup

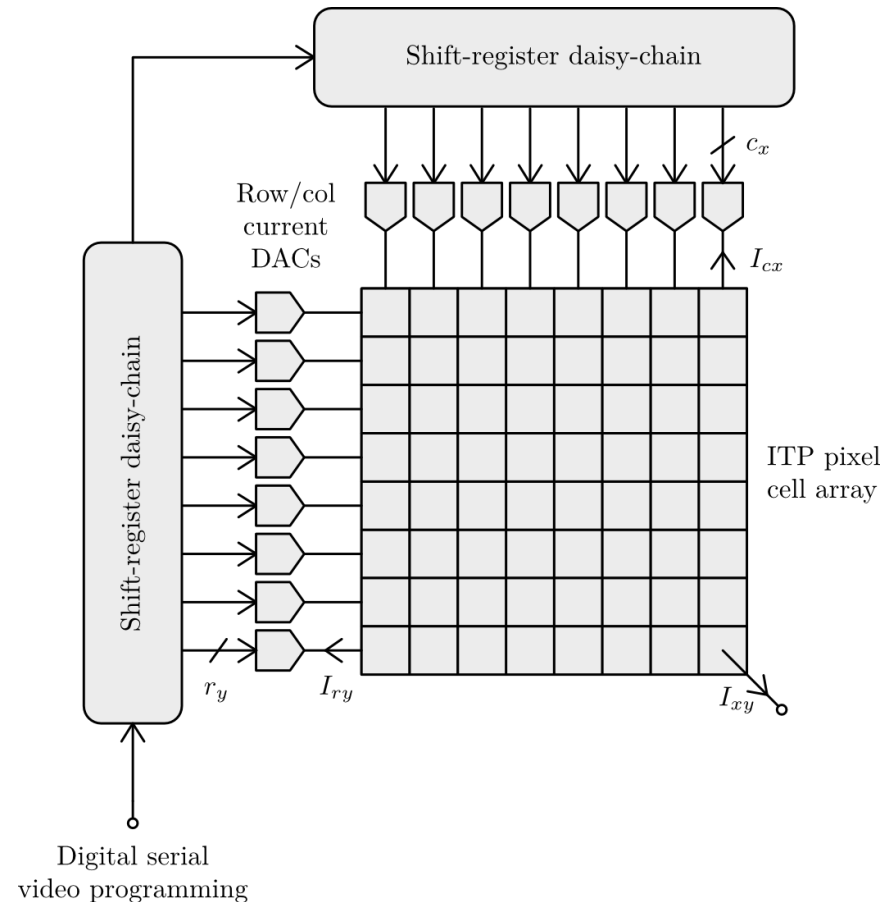


- ▲ ITP **digital current sources** ( $I_{xy}$ ) allow direct stimulation of each **individual IUT pixel**
- ▲ **Hybrid imager** prototypes can be tested before sensor integration at wafer level (e.g. IR and X-ray imagers)

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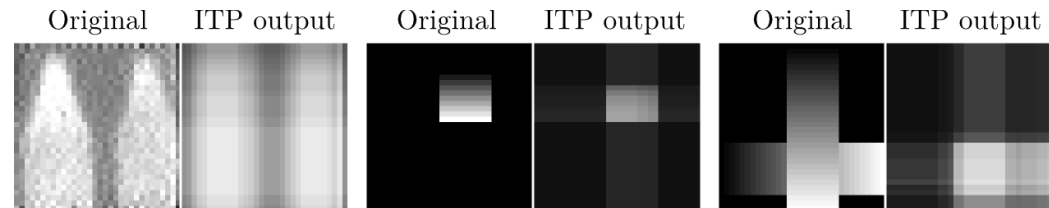
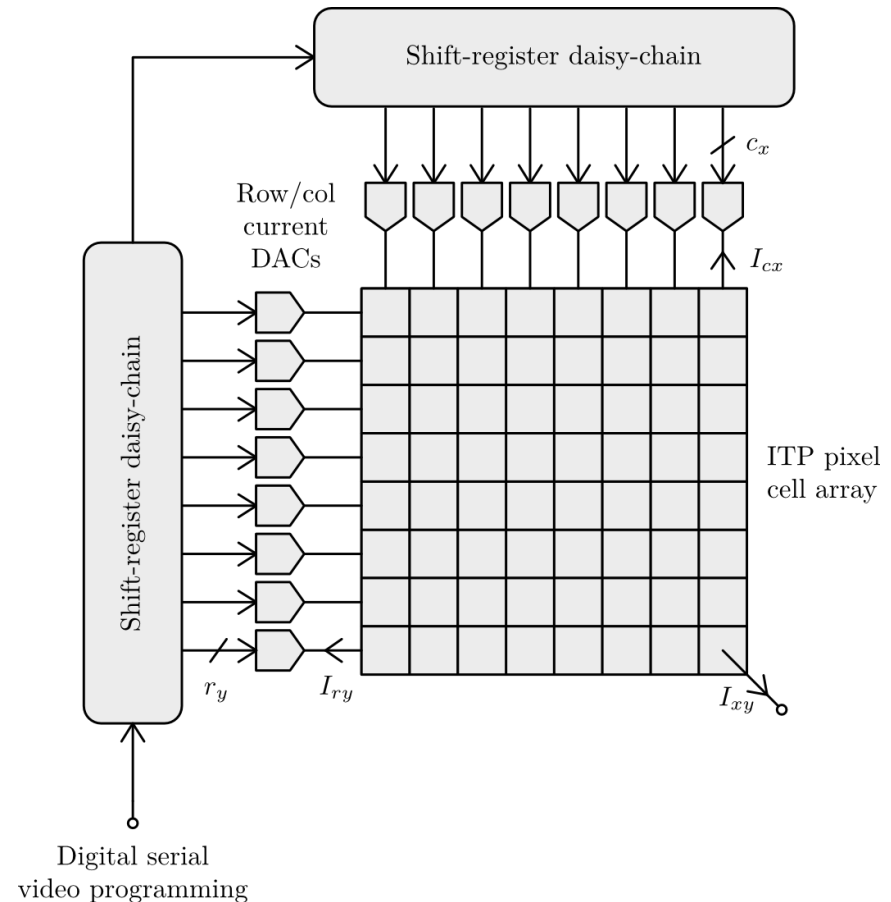
## ITP Architecture

- ▶ 2D array of **digitally controlled** current sources ( $I_{xy}$ )
- ▶  $I_{xy}$  individual value obtained as a combination of **row** ( $I_{ry}$ ) and **column** ( $I_{cx}$ ) **currents**
- ▶ Programmed at **each frame** through  $r_y$  and  $c_x$  digital codes and **peripheral current DACs**
- ▲ **Compact** pixel pitch
- ▲ Square root **scalability** with image size
- ▲ Reduced programming data size enables **high frame rates**



## ITP Architecture

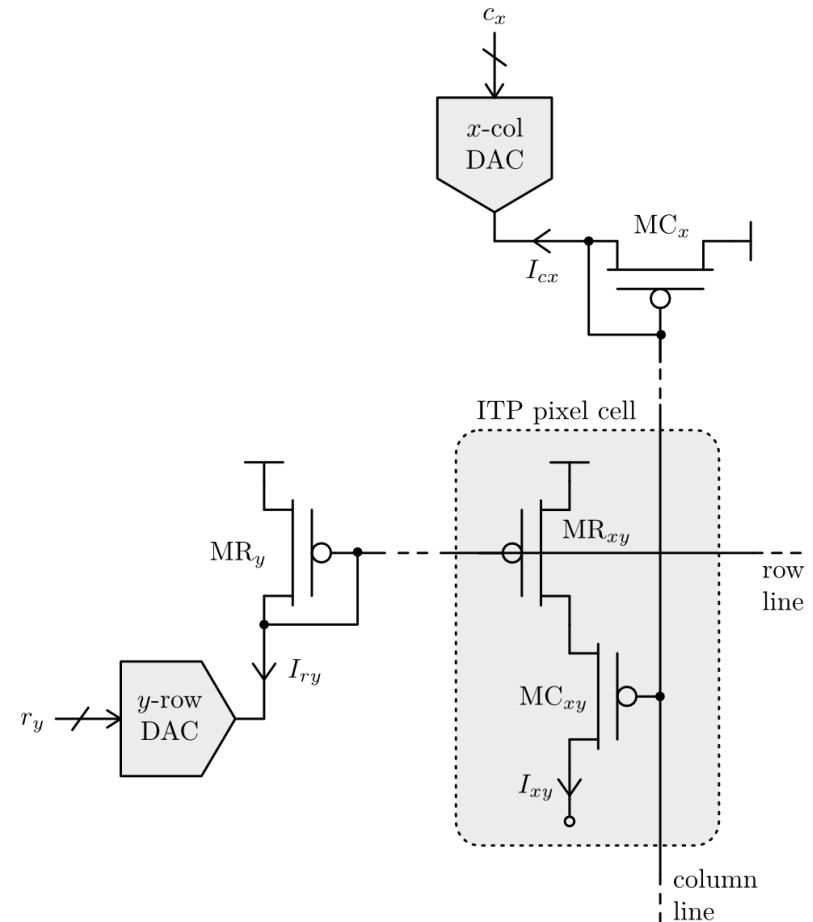
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- ▼ Synthesizable images are reduced to practical **moving test patterns** (e.g. rectangles, lines, gradients)



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## ITP Pixel Cell

- ▶ **2-transistor** only pixel
- ▶ **Matching** at row ( $MR_{xy}$ - $MR_y$ ) and column ( $MC_{xy}$ - $MC_x$ ) levels
- ▶ **Strong inversion** operation for all devices and forward saturation for  $MC_{xy}$ ,  $MR_y$  and  $MC_x$ :
- ▲ **Independence** from technology improves fixed pattern noise (FPN) and integration yield
- ▼ **Non-linear** behavior



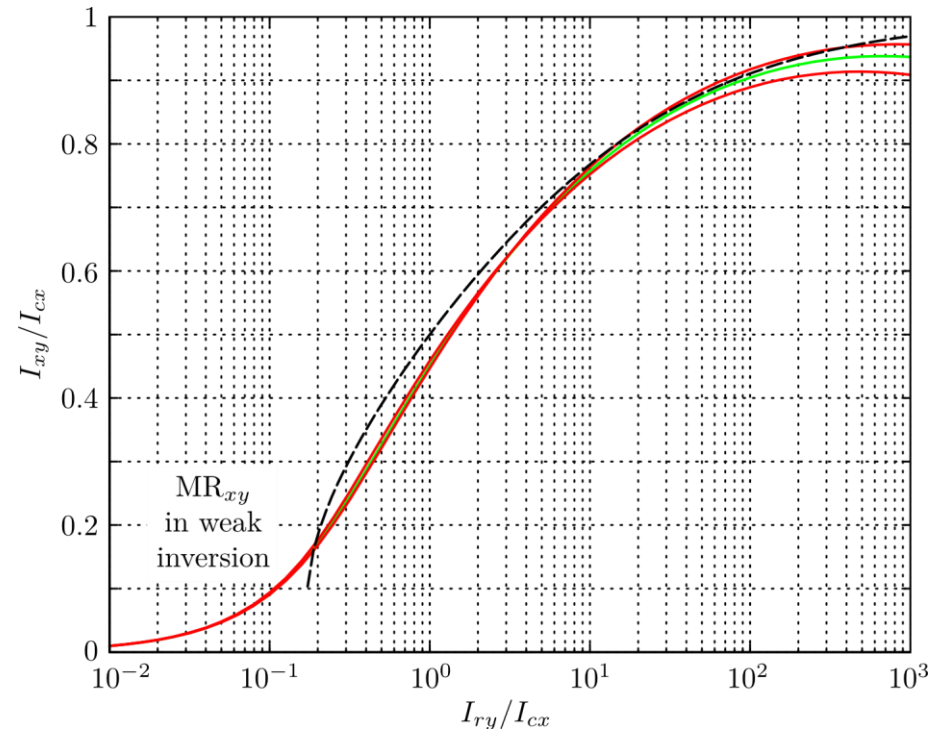
$$I_{xy} = \frac{1}{4} \left( \sqrt{I_{cx}} - \sqrt{I_{ry}} + \sqrt{I_{ry} - I_{cx} + 2\sqrt{I_{ry}I_{cx}}} \right)^2$$



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- ▲ Good agreement between **analytical-simulated** results. Linearization through digital **pre-emphasis**
- ▲ **Low sensitivity** against CMOS process corners

- ▶ **Row** control only:

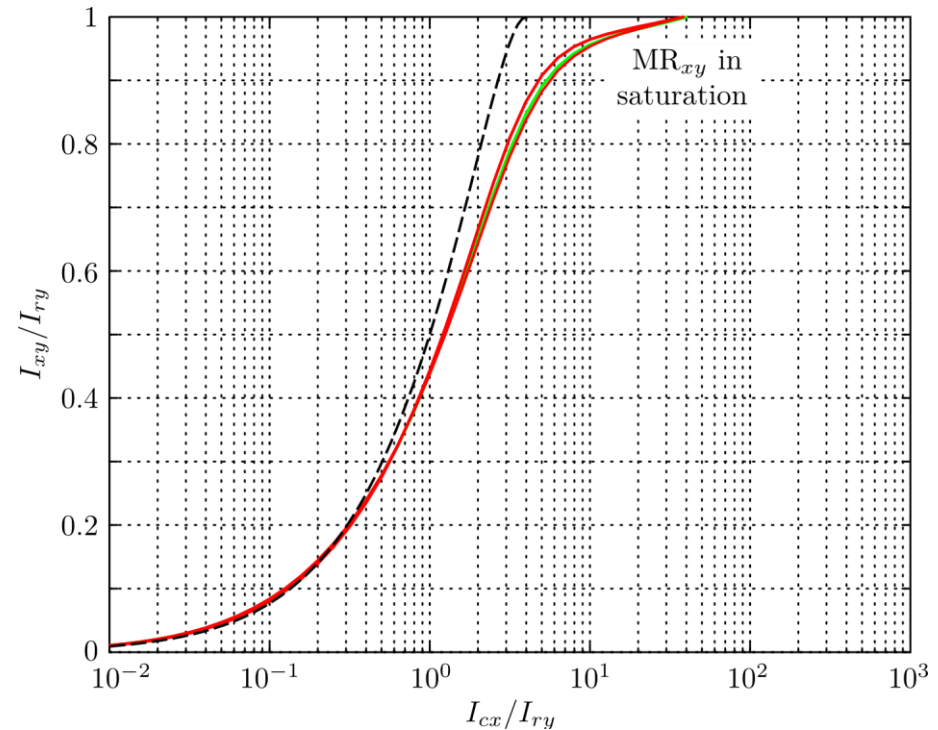


$$\frac{I_{xy}}{I_{cx}} = \frac{1}{4} \left( 1 - \sqrt{\frac{I_{ry}}{I_{cx}}} + \sqrt{\frac{I_{ry}}{I_{cx}} - 1 + 2\sqrt{\frac{I_{ry}}{I_{cx}}}} \right)^2$$

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- ▲ **Low sensitivity** against CMOS process corners

- ▶ **Column control only:**

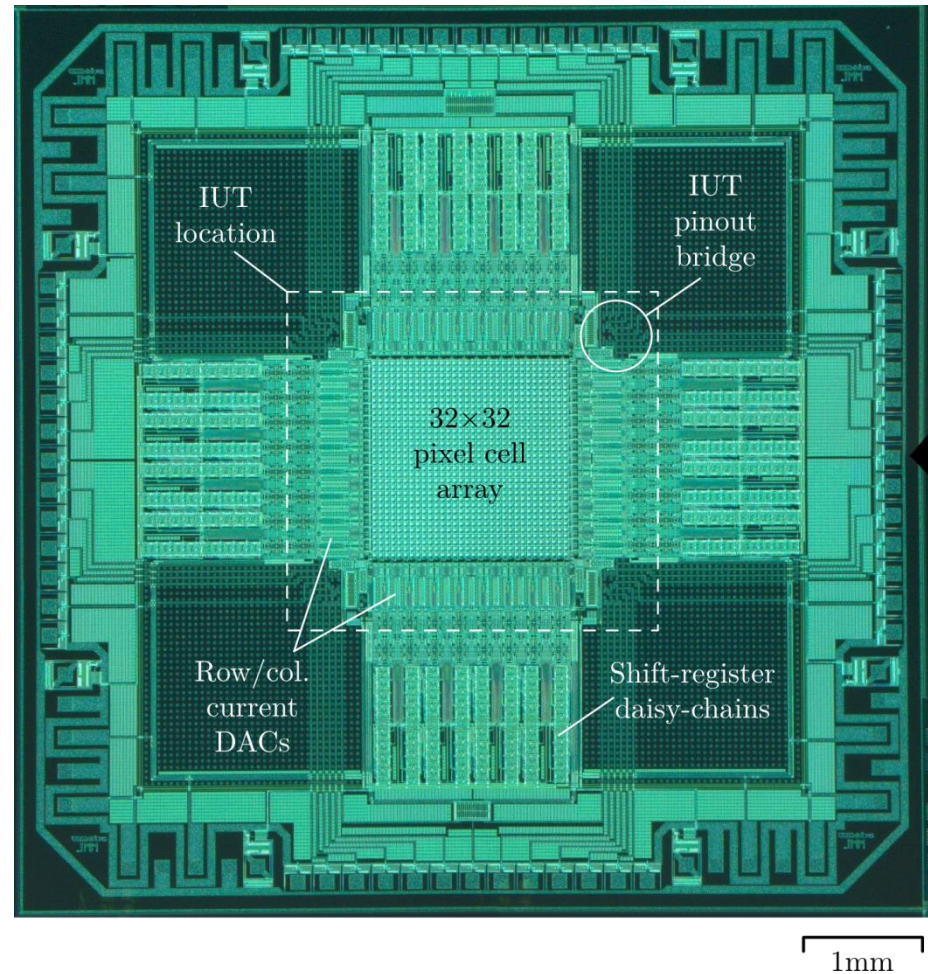
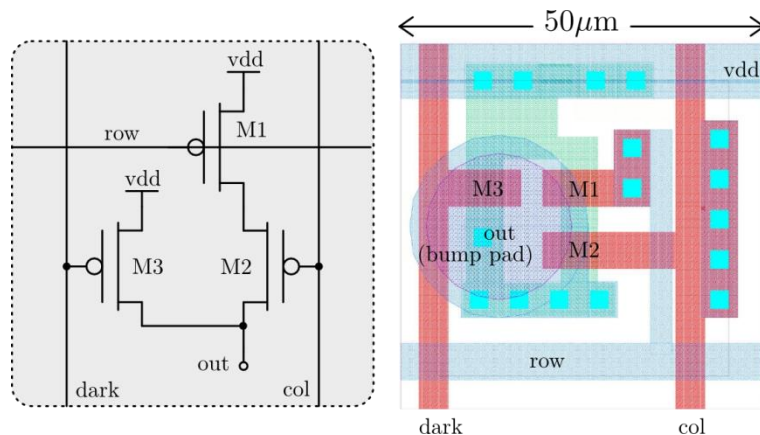


$$\frac{I_{xy}}{I_{ry}} = \frac{1}{4} \left( \sqrt{\frac{I_{cx}}{I_{ry}}} - 1 + \sqrt{1 - \frac{I_{cx}}{I_{ry}} + 2\sqrt{\frac{I_{cx}}{I_{ry}}}} \right)^2$$

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## CMOS Integration

- ▶ **32x32-pix 50 $\mu$ m-pitch** ITP
- ▶ **Low-cost** 2.5 $\mu$ m 1M CMOS tech. suitable for full-wafer flip-chip
- ▶ Global **dark current** added to pixel cell (M3)
- ▶ **4-bit** (16-level) row and column current DAC programmability

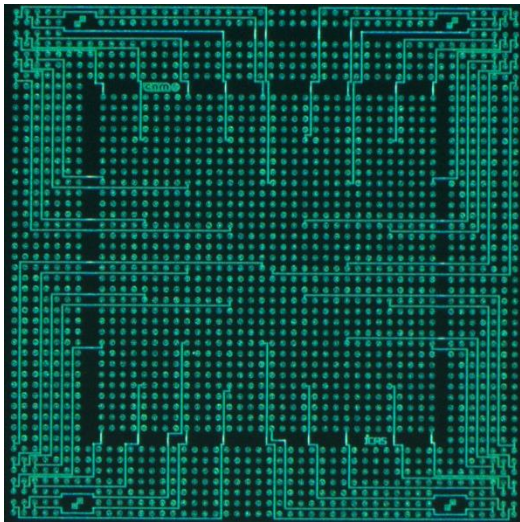


$$I_{xy} = I_{bkgd} + \frac{1}{4} \frac{I_{fs}}{16} \left( \sqrt{c_x} - \sqrt{r_y} + \sqrt{r_y - c_x + 2\sqrt{r_y c_x}} \right)^2$$

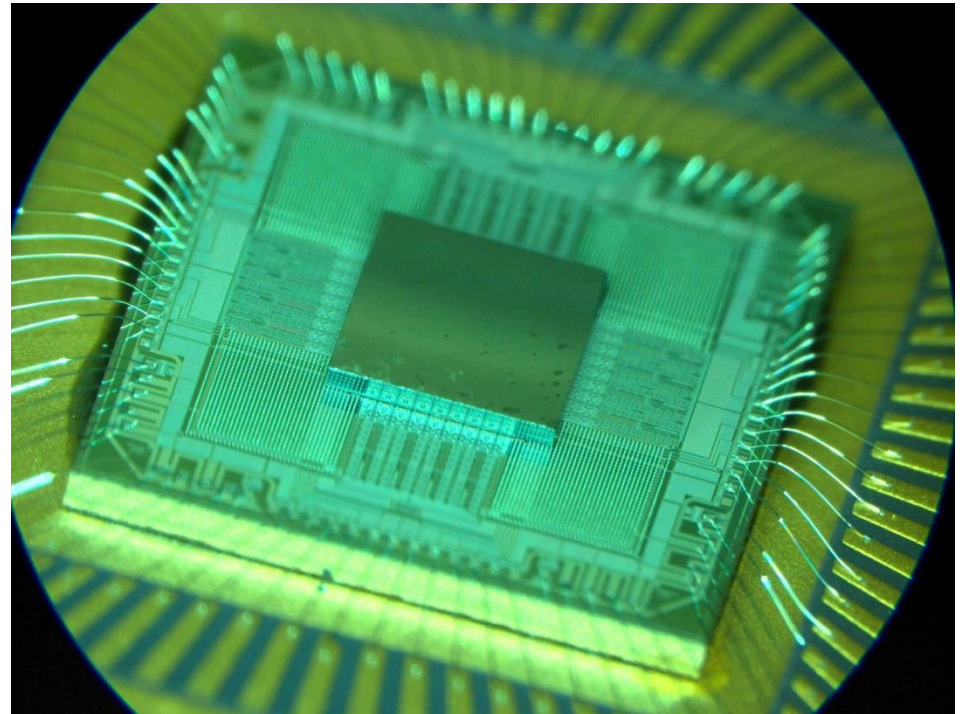


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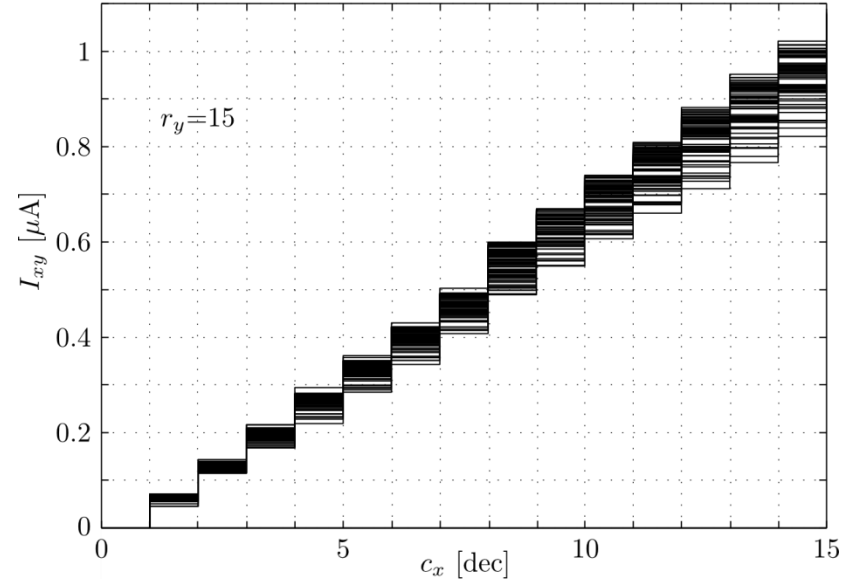
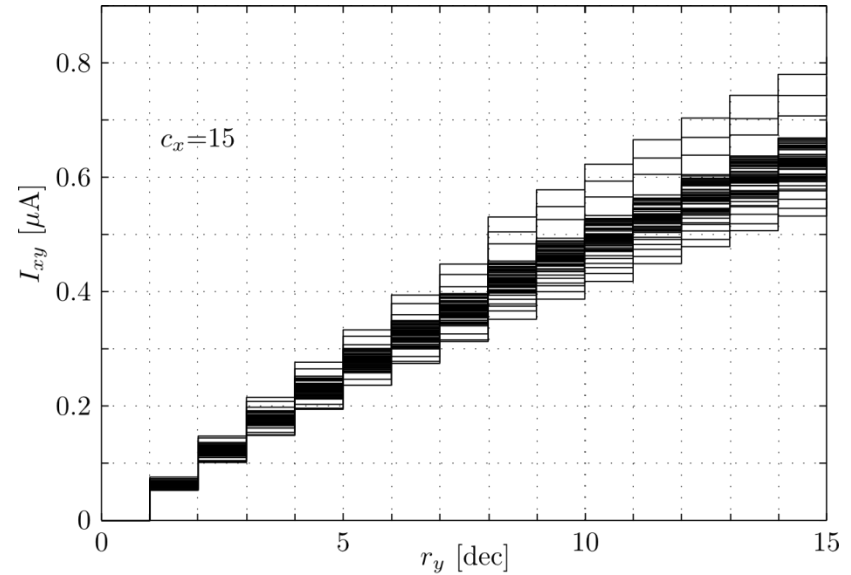
- ▲ **Phantom IUT** chip (3x3mm<sup>2</sup>) with **routing map** for the direct measurement of selected ITP pixel cells



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## Experimental Results

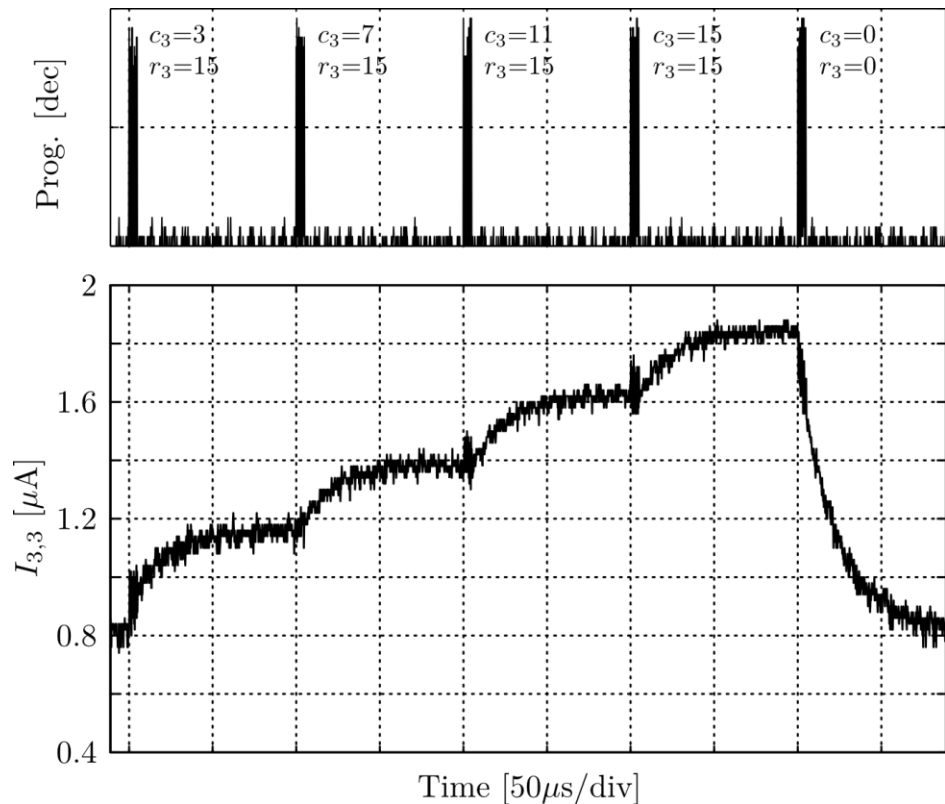
- ▲ Individual pixel current **programmability** can cover practical levels of sensor **background** and **full-scale**
- ▲ **5%<sub>rms</sub> FPN** from 50 pixel readings of 3 ITP dies



## Experimental Results

- ▲ Individual pixel current **programmability** can cover practical levels of sensor **background** and **full-scale**
- ▲ **5%<sub>rms</sub> FPN** from 50 pixel readings of 3 ITP dies
- ▲ **10kfps** rate achievable with smooth transitions

Parameter	Value	Units
Array size	32×32	pix
Pixel pitch	50	μm
Digital row/col control	4	bit
Full-scale current range	0 to 4	μA
Background current range	0 to 10	μA
Fixed pattern noise	< 5	% <sub>rms</sub>
Max. prog. rate	20	Mbps
Max. image rate	10	kfps
Supply voltage	5	V
Die area	7.2×7.2	mm <sup>2</sup>





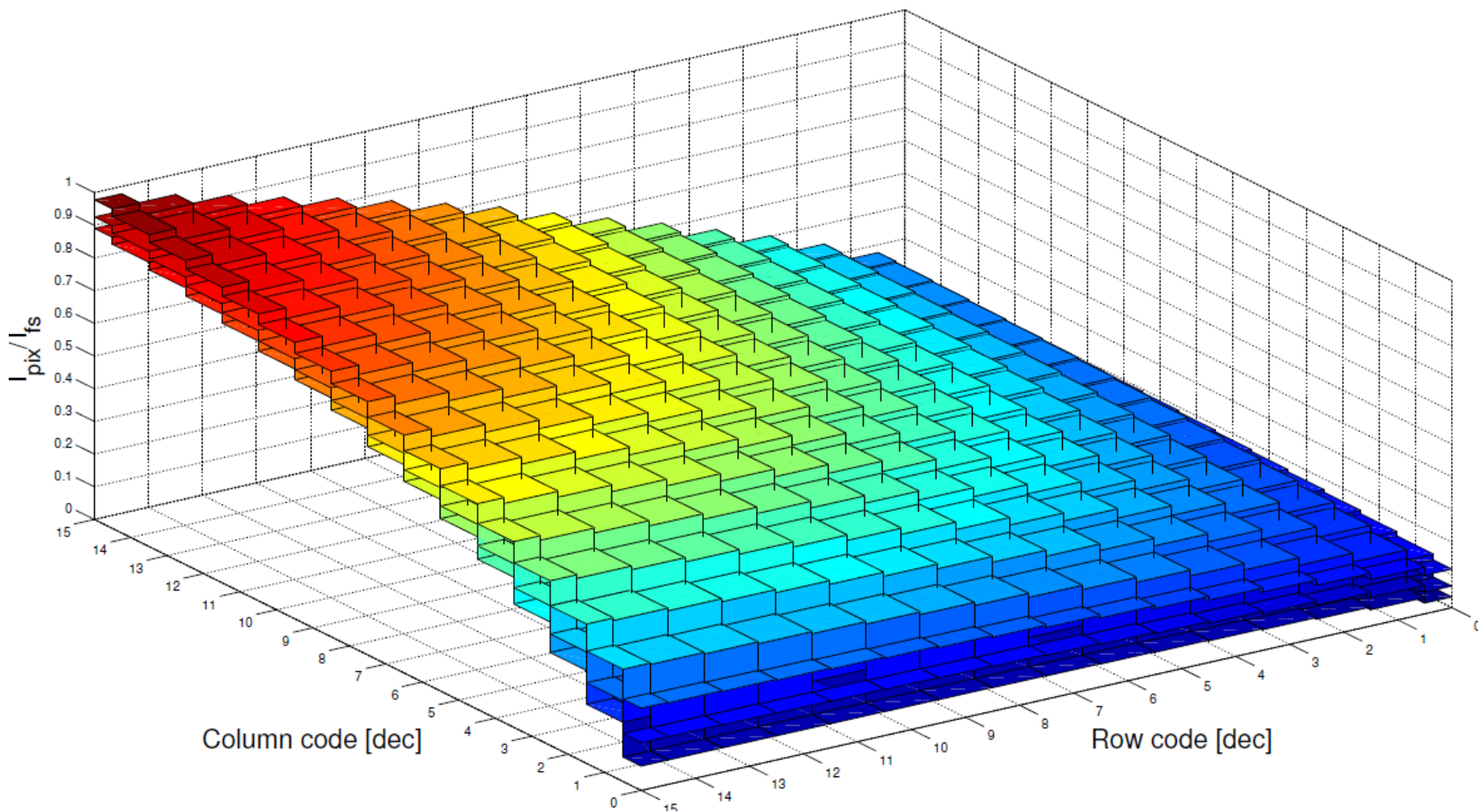
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## Conclusions

- ▶ Novel **integrated test platform** (ITP) proposal for imagers
- ▶ Direct **electrical test** of each individual imager **pixel**
- ▶ Combined row/column **digital** programmability with **low technology** sensitivity
- ▶ Synthesis of practical image **test patterns** and high-speed **motion** sequences
- ▶ **32x32-pix** 4x4-bit ITP example in **low-cost** 2.5 $\mu\text{m}$  1M CMOS technology
- ▶ **Experimental results** return  $\mu\text{A}$ -range 5%<sub>rms</sub>-FPN 10kfps performance suitable for imager testing

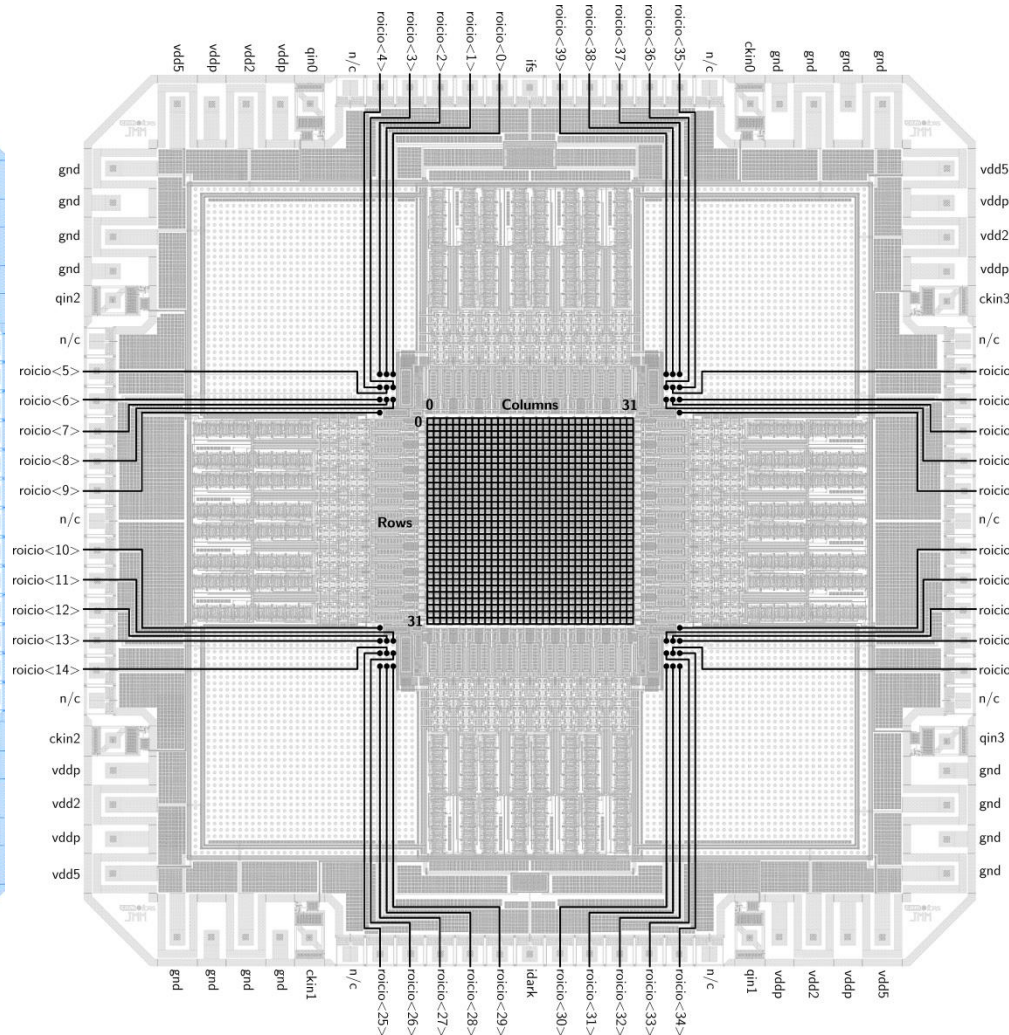
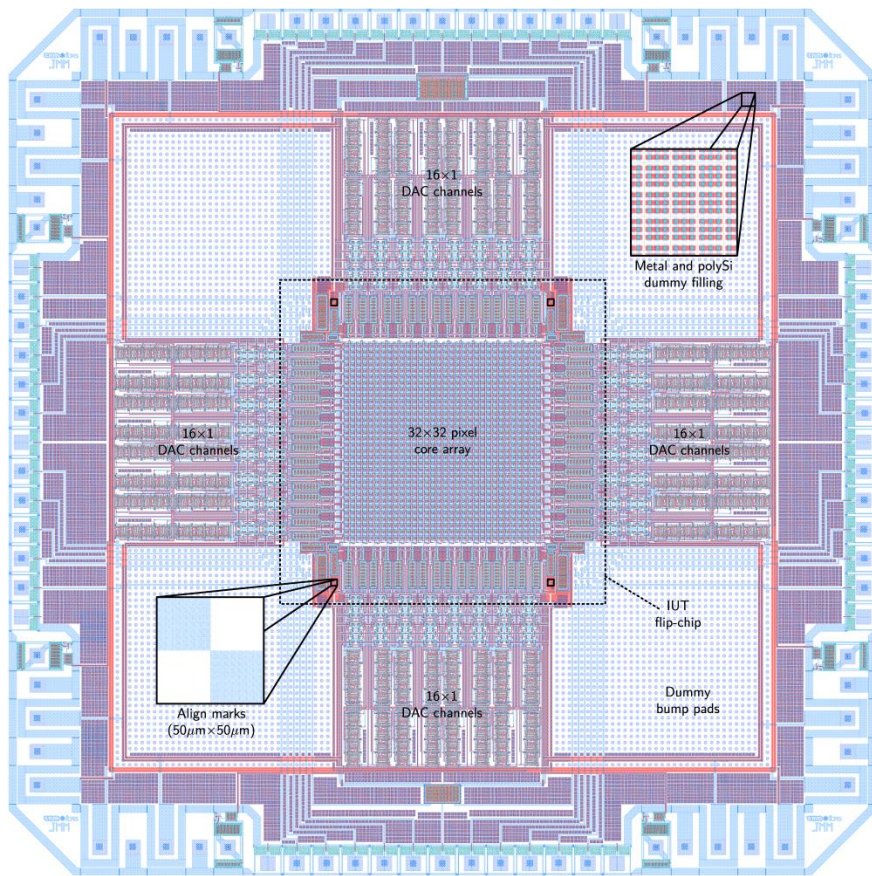
**Thanks** for your attention!!!

## $I_{\text{pix}}$ Programmability

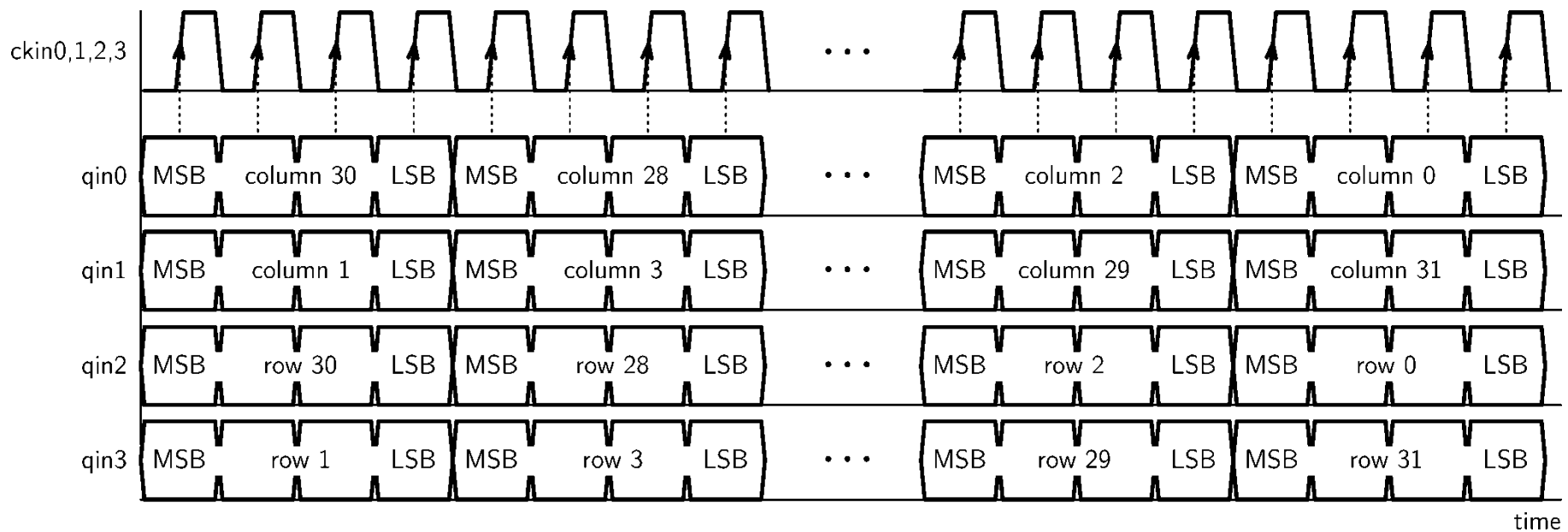




# I TP Layout

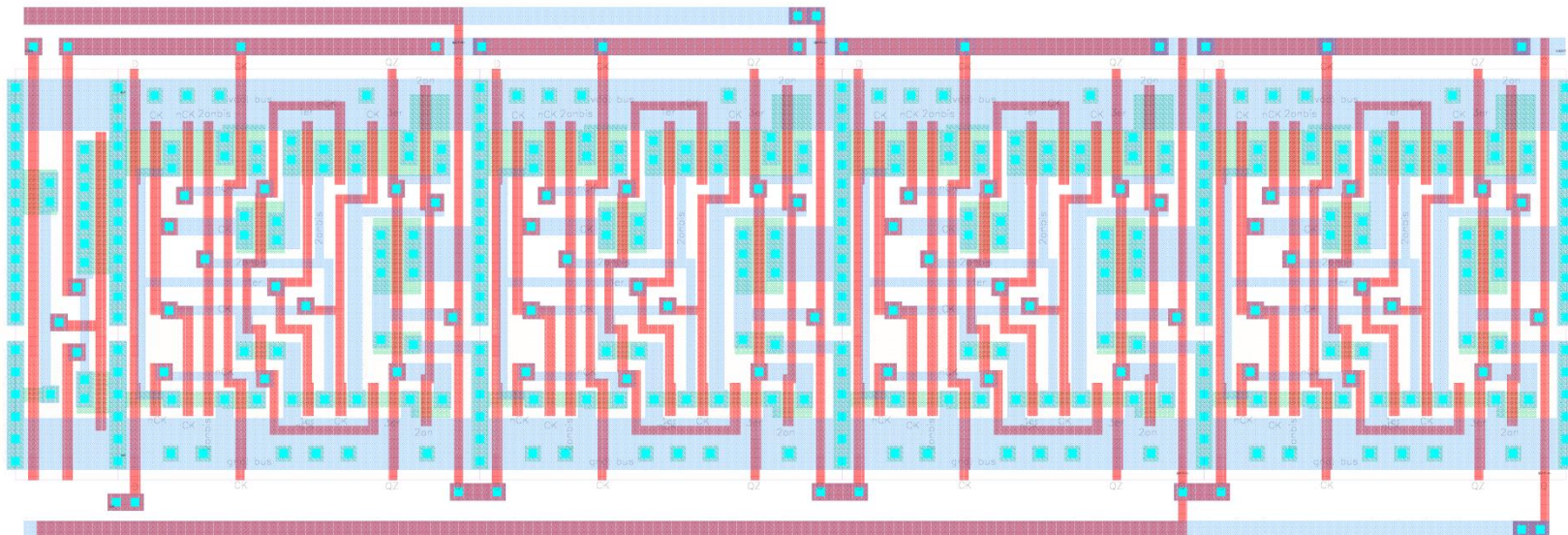
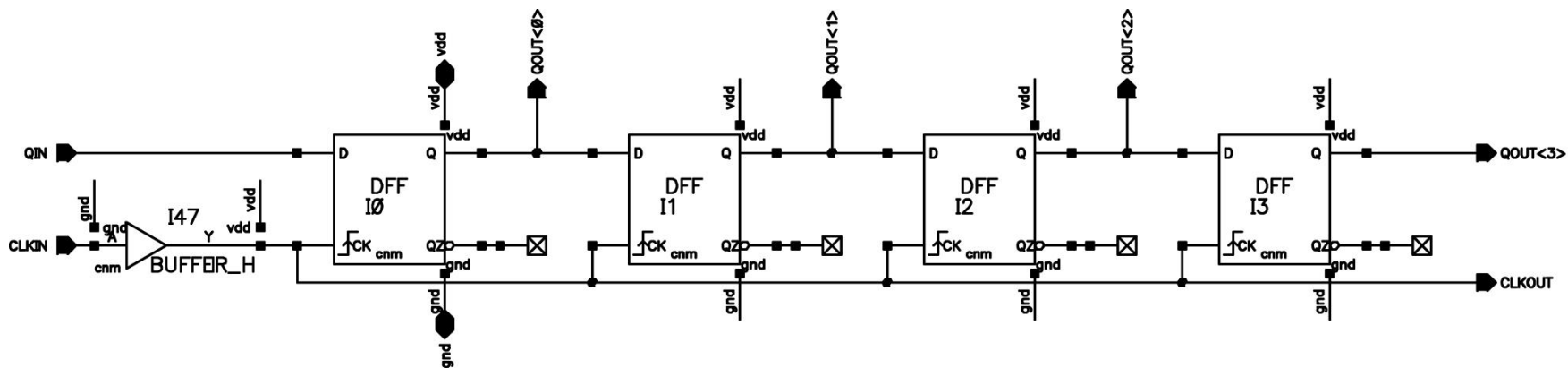


## I TP Configuration Chronogram

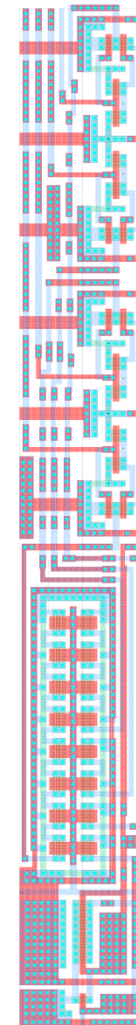
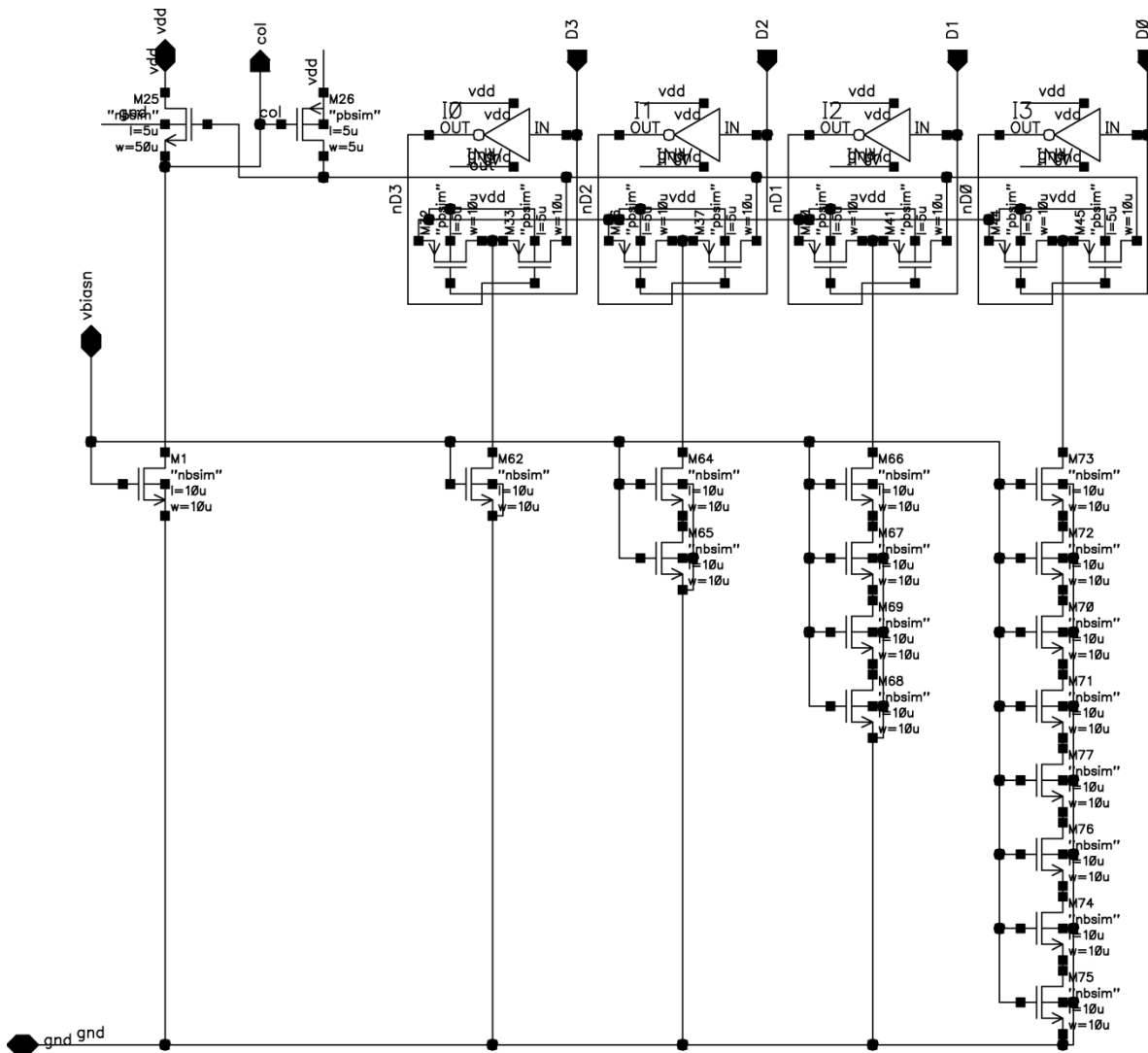




## ITP Digital Control



# ITP D/A Converter





## ITP-IUT Bump Bonding (In, SnPb)

